

1. Material Substrate GaAs (N Type)
 Epitaxial Layer GaAsP (P/N Type)

2. Electrode N(Cathode) Side Gold Alloy
 P(Anode) Side Aluminum Alloy

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F			1.68	V	IF=10mA
Reverse Voltage	V_R	5			V	IR=10uA
Power	P_O	0.4			mW	IF=10mA
Wavelength	λ_d		650		nm	IF=10mA
	$\Delta\lambda$		35		nm	IF=10mA

※ Note : LED Chip is mounted on TO-18 gold header without resin coat

4. Mechanical Data (a) Emission Area ----- 8.3mil x 8.3mil
 (b) Bottom Area ----- #####
 (c) Bonding Pad ----- 100um
 (d) Chip Thickness ----- 7mil

